

Type No.	V _{CES} (V)	I _c (A)	V _{CE(sat)} MAX.		SW TIME (MAX.)			Circuit Symbol	Package Style
			V	I _c (A)	ton (μs)	toff (μs)	tf (μs)		
MG25N1JS1	1000	±25	5	25	1	2	1	JS	19
MG25N1ZS1	1000	±25	5	25	1	2	1	ZS	19
MG25N2YS1	1000	±25×2	5	25	1	2	1	YS	19
MG50N1BS1	1000	50	5	50	1	1.5	1	BS	17
MG50N2YS1	1000	±50×2	5	50	1	1.5	1	YS	19
MG75N1BS1	1000	75	5	75	1	2	1	BS	17
MG75N2YS1	1000	±75×2	5	75	1	2	1	YS	26
MG100N2YS1	1000	±100×2	5	100	1	2	1	YS	22
MG150N2YS1	1000	±150	5	150	1.5	2	1	YS	22
MG200N1US1	1000	±200	5	200	1.5	2	1	US	21
MG300N1US1	1000	±300	5	300	1.5	2	1	US	21
MG25S2YS1 *	1400	±25×2	5	25	1	2	1	YS	19

* Under development

d) IGBT TYPE (HIGH SPEED SWITCHING TYPE)

Type No.	V _{CES} (V)	I _c (A)	V _{CE(sat)} MAX.		SW TIME (MAX.)			Circuit Symbol	Package Style
			V	I _c (A)	ton (μs)	toff (μs)	tf (μs)		
MG8J6ES1	600	±8×6	4	8	0.4	1.0	0.35	ES	16
MG15J6ES1	600	±15×6	4	15	0.4	1.0	0.35	ES	16
MG25J2YS1	600	±25×2	4	25	0.8	1.0	0.35	YS	19
MG25J2YS9	600	±25×2	4	25	0.8	1.0	0.35	YS	32
MG25J6ES1	600	±25×6	4	25	0.8	1.0	0.35	ES	20
MG50J2YS1	600	±50×2	4	50	0.8	1.0	0.35	YS	19
MG50J2YS9	600	±50×2	4	50	0.8	1.0	0.35	YS	32
MG50J6ES1	600	±50×6	4	50	0.8	1.0	0.35	ES	14
MG75J2YS1	600	±75×2	4	75	0.8	1.0	0.35	YS	19
MG75J2YS9	600	±75×2	4	75	0.8	1.0	0.35	YS	32
MG75J6ES1	600	±75×6	4	75	0.8	1.0	0.35	ES	14
MG100J2YS1	600	±100×2	4	100	0.8	1.0	0.35	YS	19
MG100J2YS9	600	±100×2	4	100	0.8	1.0	0.35	YS	32
MG100J6ES1	600	±100×6	4	100	0.8	1.0	0.35	ES	14
MG150J2YS1	600	±150×2	4	150	0.8	1.0	0.35	YS	24
MG200J2YS1	600	±200×2	4	200	0.8	1.0	0.35	YS	24
MG300J1US1	600	±300	4	300	0.8	1.0	0.35	US	21
MG300J2YS1	600	±300×2	4	300	0.8	1.0	0.35	YS	22
MG400J1US1	600	±400	4	400	0.8	1.0	0.35	US	21
MG400J1US2	600	±400	4	400	0.8	1.0	0.35	US	21
MG8Q6ES1	1200	±8×6	4	8	0.8	1.5	0.5	ES	27
MG15Q2YS9	1200	±15×2	4	15	0.8	1.5	0.5	YS	32
MG15Q6ES1	1200	±15×6	4	15	0.8	1.5	0.5	ES	27